

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 06-274409

(43)Date of publication of application : 30.09.1994

(51)Int.Cl.

G06F 12/00

G06F 12/16

G11C 16/06

(21)Application number : 05-050247

(71)Applicant : INTERNATL BUSINESS MACH  
CORP <IBM>

(22)Date of filing : 11.03.1993

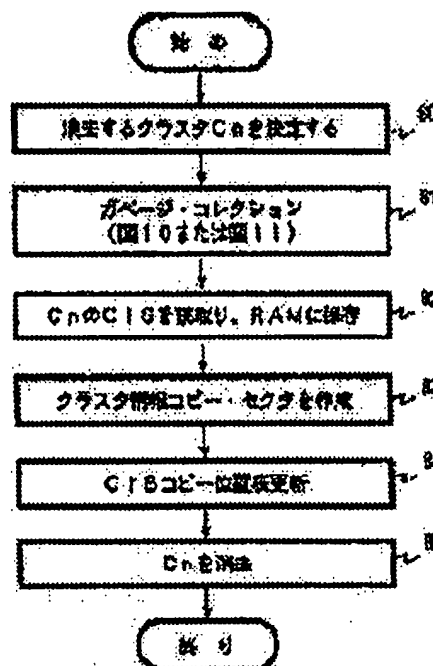
(72)Inventor : NIJIMA HIDETO  
TOYOOKA TAKASHI

(54) BATCH ERASURE TYPE NON-VOLATILE MEMORY

(57)Abstract:

PURPOSE: To enhance resistance against fault like power cutoff, etc., in a semiconductor disk device which uses a batch erasure type non-volatile memory.

CONSTITUTION: A batch erasure type non-volatile memory contains plural sectors and attribute information for recognizing their own attribute is written in every sector. As a rule, a cluster information sector is placed at the front position of a cluster to which it belongs. Then, data sector is placed in a data area which is an area except the front position of a cluster. A controller connected to the memory produces a cluster information copy sector in a data area at the time of cluster erasure, reconstitutes cluster management information from the cluster information copy sector and produces a cluster information sector at the time of cluster initialization.



## LEGAL STATUS

[Date of request for examination] 15.06.1993

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3078946

[Date of registration] 16.06.2000

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's]